

CMPSH-3CG**SURFACE MOUNT
DUAL, COMMON CATHODE
SILICON SCHOTTKY DIODES**www.centrasemi.com**DESCRIPTION:**

The CENTRAL SEMICONDUCTOR CMPSH-3CG is a dual, common cathode Silicon Schottky diode designed for surface mount fast switching applications requiring a low forward voltage drop.

MARKING CODE: DB2G**SOT-23 CASE**

• Device is **Halogen Free** by design

MAXIMUM RATINGS: ($T_A=25^\circ\text{C}$)

Peak Repetitive Reverse Voltage
Continuous Forward Current
Peak Repetitive Forward Current
Peak Forward Surge Current, $t_p=10\text{ms}$
Power Dissipation
Operating and Storage Junction Temperature
Thermal Resistance

SYMBOL

V_{RRM}	30
I_F	100
I_{FRM}	350
I_{FSM}	750
P_D	350
T_J, T_{stg}	-65 to +150
θ_{JA}	357

UNITS

V
mA
mA
mA
mW
$^\circ\text{C}$
$^\circ\text{C}/\text{W}$

ELECTRICAL CHARACTERISTICS PER DIODE: ($T_A=25^\circ\text{C}$ unless otherwise noted)

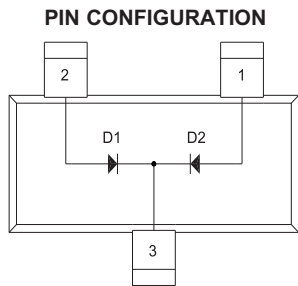
SYMBOL	TEST CONDITIONS	MIN	TYP	MAX	UNITS
I_R	$V_R=25\text{V}$		90	500	nA
I_R	$V_R=25\text{V}, T_A=100^\circ\text{C}$		25	100	μA
BV_R	$I_R=100\mu\text{A}$	30			V
V_F	$I_F=2.0\text{mA}$		0.29	0.33	V
V_F	$I_F=15\text{mA}$		0.40	0.45	V
V_F	$I_F=100\text{mA}$		0.74	1.00	V
C_T	$V_R=1.0\text{V}, f=1.0\text{MHz}$		7.0		pF
t_{rr}	$I_F=I_R=10\text{mA}, I_{rr}=1.0\text{mA}, R_L=100\Omega$			5.0	ns

R1 (27-January 2010)

CMP5H-3CG
SURFACE MOUNT
DUAL, COMMON CATHODE
SILICON SCHOTTKY DIODES



SOT-23 CASE - MECHANICAL OUTLINE



LEAD CODE:

- 1) Anode D2
- 2) Anode D1
- 3) Cathode D1, D2

MARKING CODE: DB2G

DIMENSIONS				
SYMBOL	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	0.003	0.007	0.08	0.18
B	0.006	-	0.15	-
C	-	0.005	-	0.13
D	0.035	0.043	0.89	1.09
E	0.110	0.120	2.80	3.05
F	0.075		1.90	
G	0.037		0.95	
H	0.047	0.055	1.19	1.40
I	0.083	0.098	2.10	2.49
J	0.014	0.020	0.35	0.50

SOT-23 (REV: R3)

R1 (27-January 2010)